# 2SB1073

# Silicon PNP epitaxial planar type

## For low-frequency amplification

## ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- ullet Large peak collector current  $I_{CP}$
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-30	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-20	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V	
Collector current	$I_C$	-4	A	
Peak collector current	I <sub>CP</sub>	-7	A	
Collector power dissipation *	P <sub>C</sub>	1	W	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +1 <b>5</b> 0	°C	

Note) \*: Print circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion

# Unit: mm 4.5±0.1 1.6±0.2 1.5±0.1 1.

Marking Symbol: J

# ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emiter open)	V <sub>CBO</sub>	$I_{\rm C} = -10$ pA, $I_{\rm E} = 0$	-30			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm Q} = 1 \text{ mA}, I_{\rm B} = 0$	-20			V
Emiter-base voltage (Collector open)	$V_{EBO}$	$I_{\rm E} = -10$ µA, $I_{\rm C} = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBQ}$	$V_{CB} = -30 \text{ V}, I_E = 0$			- 0.1	μΑ
Emitter-base cutoff current (Collector open)	IEBO	$V_{EB} = -7 \text{ V}, I_C = 0$			- 0.1	μΑ
Forward current transfer ratio *1,2	h <sub>FE</sub>	$V_{CE} = -2 \text{ V}, I_{C} = -2 \text{ A}$	120		315	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -3 A, I_B = -0.1 A$		- 0.6	-1.0	V
Transition frequency	$f_T$	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		40		pF
(Common base, input open circuited)						

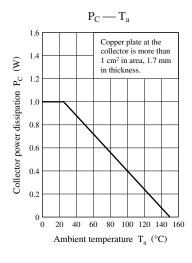
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

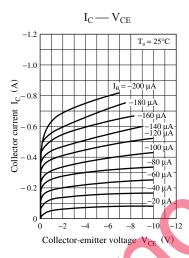
## 2. \*1: Pulse measurement

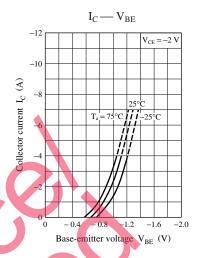
### \*2: Rank classification

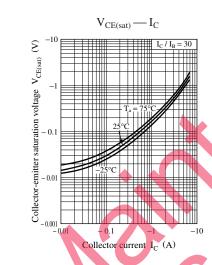
Rank	Q	R
$h_{FE}$	120 to 205	180 to 315

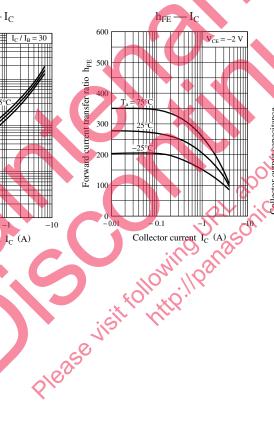
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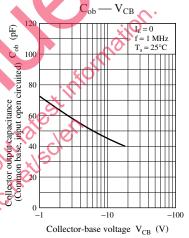












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